

# Taiwan Goodark Technology Co.,Ltd

CESD12VCP

# **ESD Protection Diodes**

#### DESCRIPTION

The CESD12VCP is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.



#### **FEATURES**

- Stand-off Voltage: 12 V
- Low Leakage
- Response Time is Typically < 1 ns</li>
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices



#### Maximum Ratings @T<sub>A</sub>=25℃

Parameter			Limits	Unit	
IEC61000-4-2(ESD)	Air		±15	IV.	
350 441	Contact		±8.0	KV	
ESD voltage per h		16	KV		
Total power dissipation on FR-5 board (Not	PD	225	mW		
Thermal Resistance Junction-to-Ambient	R <sub>⊝JA</sub>	556	°C/W		
Lead Solder Temperature - Maximum (10	TL	260	°C		
Junction and Storage temperature range	Tj, Tstg	-55 ~ +150	°C		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended. Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.



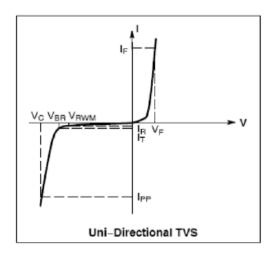
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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit fied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter					
IPP	Maximum Reverse Peak Pulse Current					
Vc	Clamping Voltage @ I <sub>PP</sub>					
V <sub>RWM</sub>	Working Peak Reverse Voltage					
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>					
$V_{BR}$	Breakdown Voltage @ I⊤					
I <sub>T</sub>	Test Current					
I <sub>F</sub>	Forward Current					
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>					
P <sub>pk</sub>	Peak Power Dissipation					
С	Max. Capacitance $@V_R=0$ and $f=1MHz$					



## **ELECTRICAL CHARACTERISTICS** ( $T_A$ = 25°C unless otherwise noted, $V_F$ = 0.9 V Max. @ $I_F$ = 10mA for all types)

Device*	Device Marking -	V <sub>RWM</sub> (V)	I <sub>R</sub> (μ Α) @ V <sub>RWM</sub>	V <sub>BR</sub> (V) @ Ι <sub>τ</sub> (Note 2)		Ι <sub>τ</sub>	Vc @IPP =1 A	Max I <sub>PP</sub> <sup>↑</sup>	P <sub>pk</sub> † (W)	C (pF) Pin 1 to 3
		Max	Max	Min	Max	mA	ν	Α	Max	Тур
CESD12VCP	12L	12	1.0	13.3	15.75	1.0	19	11.2	300	95

<sup>\*</sup>Other voltages available upon request.

<sup>+</sup>Surge current waveform per Figure 3

<sup>2.</sup> V<sub>BR</sub> is measured with a pulse test current I<sub>T</sub> at an ambient temperature of 25°C.